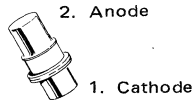


1N5150A (SILICON)

1N5153A

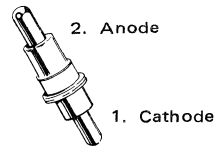
1N5155A

Silicon high-frequency step-recovery power varactor devices optimized for critical multiplier applications requiring tight control of junction capacitance and power dissipation.



CASE 46

1N5155A



CASE 47

1N5150A

1N5153A

MAXIMUM RATINGS

Rating	Symbol	1N5150A	1N5153A	1N5155A	Unit
Reverse Voltage	V_R	80	75	35	Vdc
Forward Current	I_F	1000	250	200	mAdc
RF Power Input	P_{in}	40	15	7.0	Watts
Total Device Dissipation @ $T_C = 25^\circ C$ Derate above $25^\circ C$	P_D	29.2 167	11.7 66.7	8.75 50	Watts mW/ $^\circ C$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	← -65 to +200 →			$^\circ C$

1N5150A, 1N5153A, 1N5155A (continued)

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristics	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage ($I_R = 10 \mu\text{Adc}$)	V_R				Vdc
1N5150A		80	-	-	
1N5153A		75	-	-	
1N5155A		35	-	-	
Reverse Current ($V_R = 70 \text{ Vdc}$)	I_R				μAdc
1N5150A		-	-	2.0	
($V_R = 70 \text{ Vdc}$, $T_A = 150^\circ\text{C}$)		-	-	100	
1N5153A		-	-	1.0	
($V_R = 60 \text{ Vdc}$)		-	-	100	
1N5155A		-	-	1.0	
($V_R = 26 \text{ Vdc}$)		-	-	100	
1N5155A		-	-	100	
($V_R = 26 \text{ Vdc}$, $T_A = 150^\circ\text{C}$)		-	-	100	
Series Resistance ($V_R = 6.0 \text{ Vdc}$, $f = \text{self-resonant frequency}$)	R_S				Ohms
1N5150A		-	0.25	-	
1N5153A		-	0.5	-	
1N5155A		-	0.9	-	
Series Inductance	L_S				nH
1N5150A		-	1.5	-	
1N5153A		-	1.7	-	
1N5155A		-	0.9	-	
Diode Capacitance ($C_J + C_C$) ($V_R = 6.0 \text{ Vdc}$, $f = 1.0 \text{ MHz}$)	C_T				pF
1N5150A		10.8	-	13.2	
1N5153A		5.8	-	7.0	
1N5155A		1.71	-	2.09	
Figure of Merit ($V_R = 6.0 \text{ Vdc}$, $f = 50 \text{ MHz}$)	Q				-
1N5150A		-	800	-	
1N5153A		-	1100	-	
1N5155A		-	1700	-	
Thermal Resistance	θ_{JC}				$^\circ\text{C/W}$
1N5150A		-	-	6.0	
1N5153A		-	-	15	
1N5155A		-	-	20	

FUNCTIONAL TEST

1N5150A

RF Power Output	$P_{in} = 37 \text{ W}$, $f_{in} = 500 \text{ MHz}$,	P_{out}	25.1	-	-	Watts
Doubling Efficiency	$f_{out} = 1.0 \text{ GHz}$	η	68	-	-	%

1N5153A

RF Power Output	$P_{in} = 12 \text{ W}$, $f_{in} = 1.0 \text{ GHz}$,	P_{out}	7.2	-	-	Watts
Doubling Efficiency	$f_{out} = 2.0 \text{ GHz}$	η	60	-	-	%

1N5155A

RF Power Output	$P_{in} = 5.0 \text{ W}$, $f_{in} = 2.0 \text{ GHz}$,	P_{out}	2.0	-	-	Watts
Tripling Efficiency	$f_{out} = 6.0 \text{ GHz}$	η	40	-	-	%

For typical curves and test circuits, see the following data sheets: 1N5149-1N5150, 1N5153, and 1N5155.